

Product Summary

BV_{DSS}	R_{DS(on)} max	I_D T_A = +25°C
70V	0.13Ω @ V _{GS} = 10V	3.8A

Description and Applications

This new generation of trench MOSFETs utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high-efficiency, low-voltage power management applications.

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor controls
- Class-D audio output stages

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under separate datasheet ([ZXMN7A11GQ](#))**

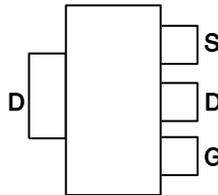
Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 Ⓢ
- Weight: 0.112 grams (Approximate)

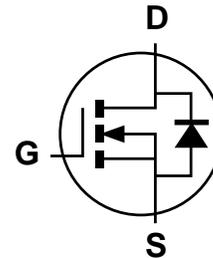
SOT223 (Type DN)



Top View



Pin Out - Top View



Equivalent Circuit

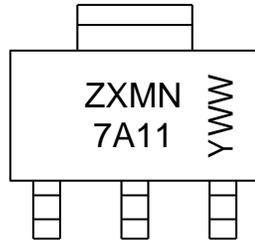
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
ZXMN7A11GTA	SOT223 (Type DN)	1,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

SOT223 (Type DN)



ZXMN 7A11 = Product Type Marking Code
 YWW = Date Code Marking
 Y or \bar{Y} = Last Digit of Year (ex: 3 = 2023)
 WW or \bar{WW} = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

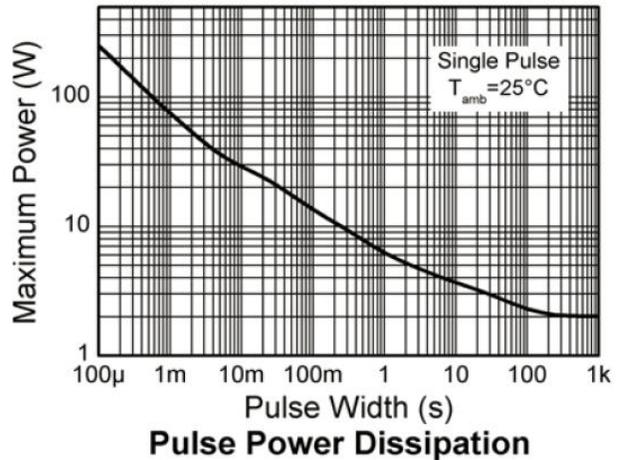
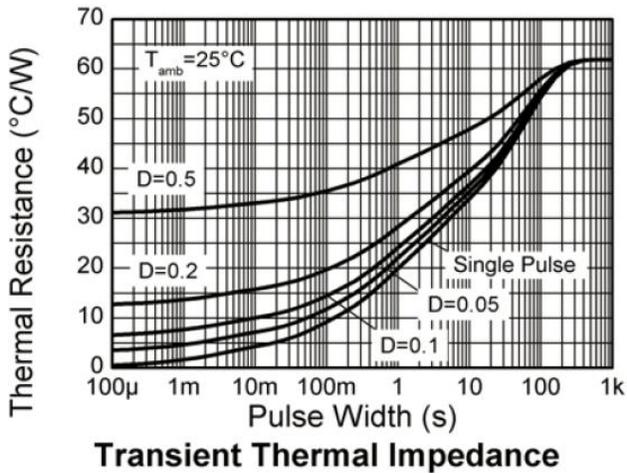
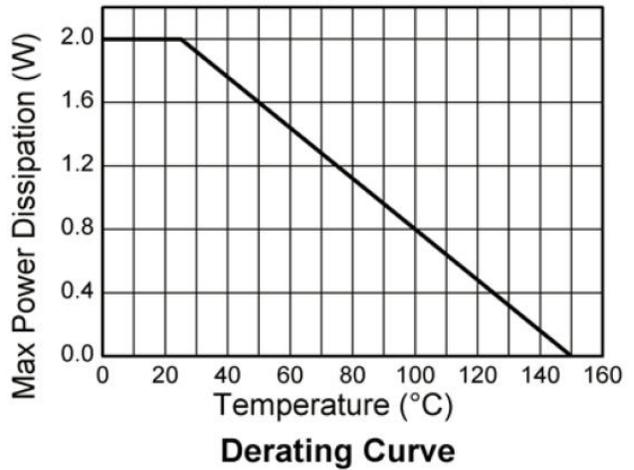
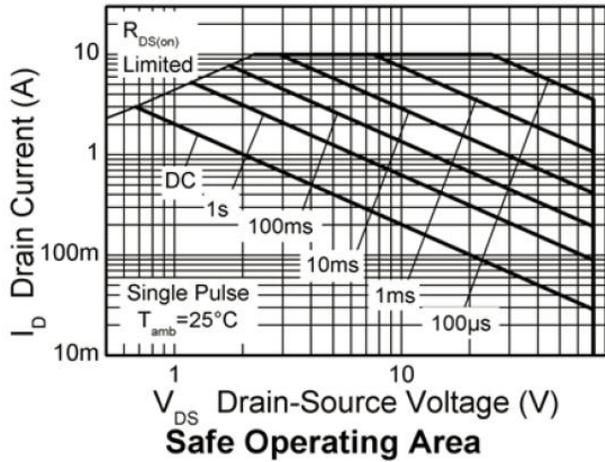
Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	70	V
Gate-Source Voltage	V _G	±20	V
Continuous Drain Current, V _{GS} = 10V	I _D	T _A = +25°C (Note 6)	3.8
		T _A = +70°C (Note 6)	3.0
		T _A = +25°C (Note 5)	2.7
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	3.8	A
Pulsed Drain Current	I _{DM}	10	A
Pulsed Source Current (Body Diode)	I _{SM}	10	A

Thermal Resistance (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation at T _A = +25°C (Note 5)	P _D	2.0	W
Linear Derating Factor (Note 5)		16	mW/°C
Total Power Dissipation at T _A = +25°C (Note 6)	P _D	3.9	W
Linear Derating Factor (Note 6)		31	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	32	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 6. For a device surface mounted on FR4 PCB measured at t ≤ 5 sec.
 7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10μs - pulse width limited by maximum junction temperature.

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

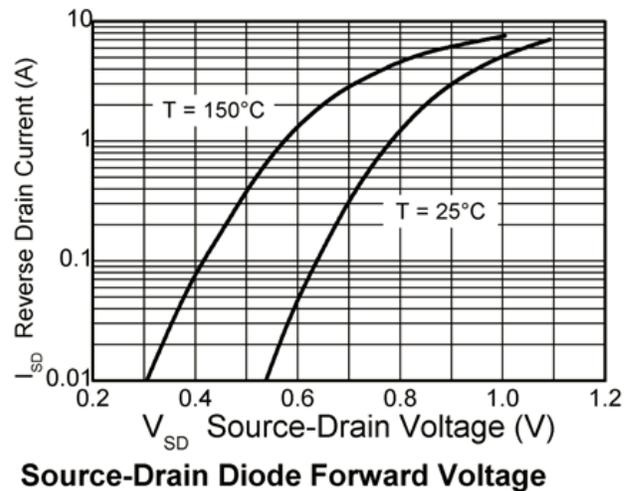
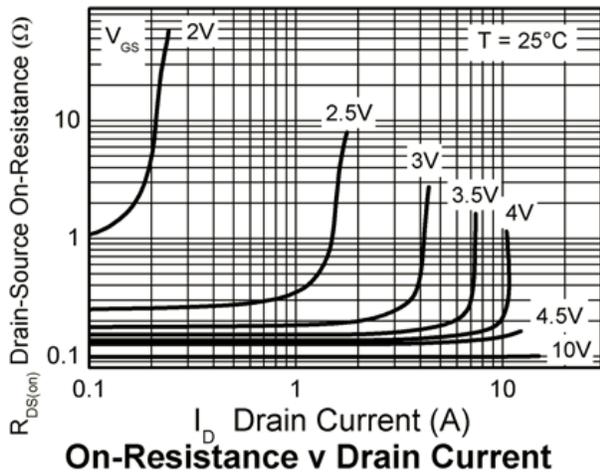
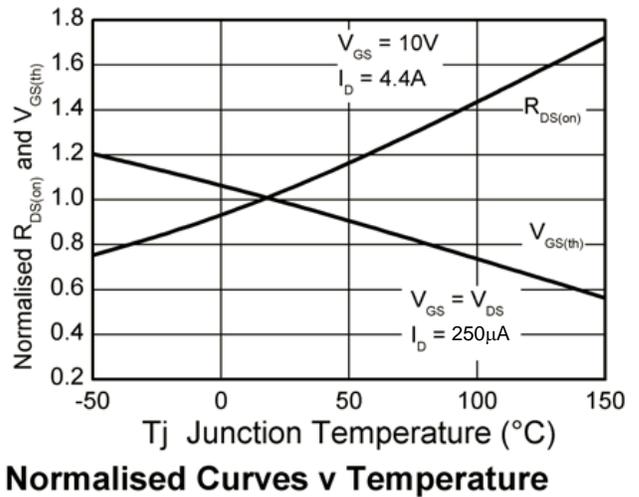
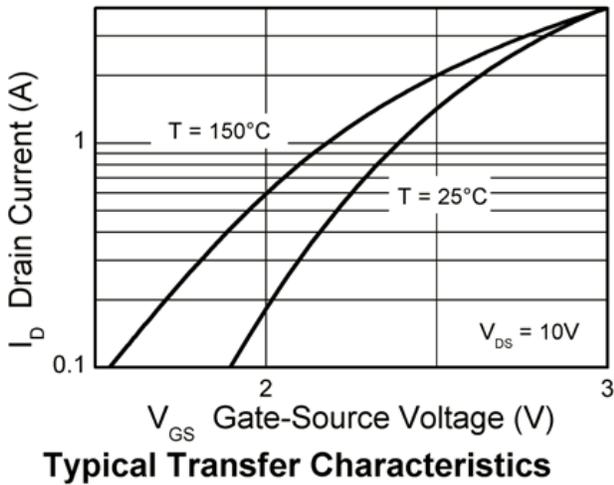
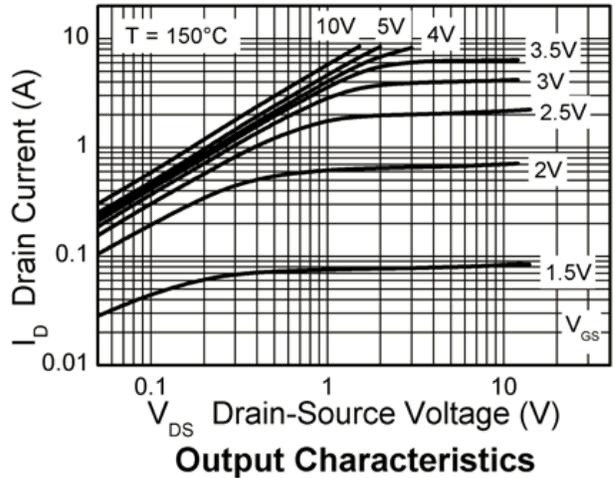
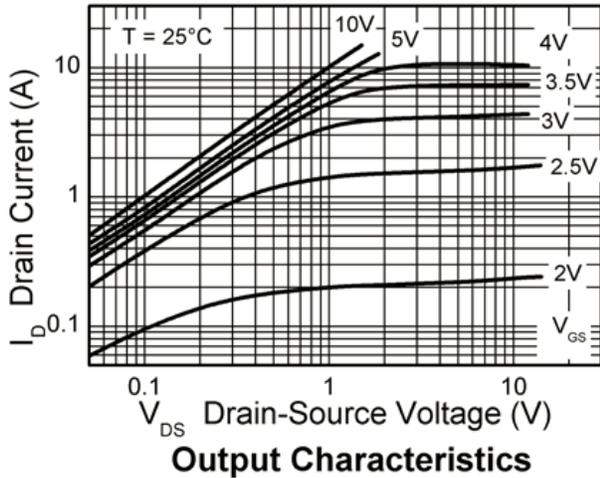


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

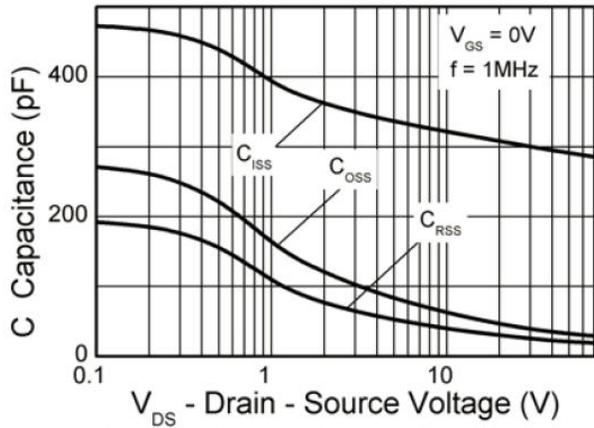
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	70	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 70V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance (Note 8)	R _{DS(on)}	—	—	0.13	Ω	V _{GS} = 10V, I _D = 4.4A
		—	—	0.19		V _{GS} = 4.5V, I _D = 3.8A
Forward Transfer Admittance	g _{fs}	—	4.66	—	S	V _{DS} = 15V, I _D = 4.4A
Diode Forward Voltage (Note 8)	V _{SD}	—	0.85	0.95	V	T _J = +25°C, V _{GS} = 0V, I _S = 2.5A
DYNAMIC CHARACTERISTICS (Notes 9 & 10)						
Input Capacitance	C _{iss}	—	298	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	35	—		
Reverse Transfer Capacitance	C _{rss}	—	21	—		
Total Gate Charge	Q _g	—	4.35	—	nC	V _{DS} = 35V, V _{GS} = 5.0V, I _D = 4.4A
Total Gate Charge	Q _g	—	7.4	—	nC	V _{DS} = 35V, V _{GS} = 10V, I _D = 4.4A
Gate-Source Charge	Q _{gs}	—	1.06	—		
Gate-Drain Charge	Q _{gd}	—	1.8	—		
Turn-On Delay Time	t _{D(on)}	—	1.9	—	ns	V _{DS} = 35V, V _{GS} = 10V, I _D = 1A, R _G ≅ 6.0Ω
Turn-On Rise Time	t _r	—	2	—		
Turn-Off Delay Time	t _{D(off)}	—	11.5	—		
Turn-Off Fall Time	t _f	—	5.8	—		
Body Diode Reverse Recovery Time	t _{rr}	—	19.8	—	ns	T _J = +25°C, I _S = 2.5A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	14	—	nC	

- Notes:
8. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.
 9. Switching characteristics are independent of operating junction temperature.
 10. For design aid only, not subject to production testing.

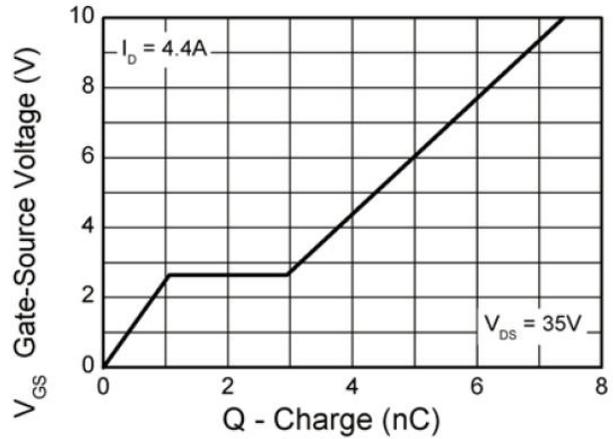
Typical Characteristics



Typical Characteristics (continued)



Capacitance v Drain-Source Voltage

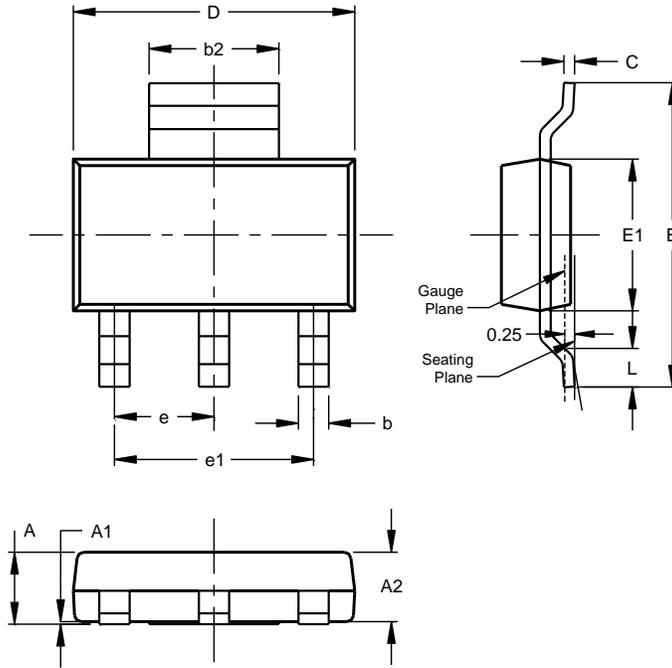


Gate-Source Voltage v Gate Charge

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)

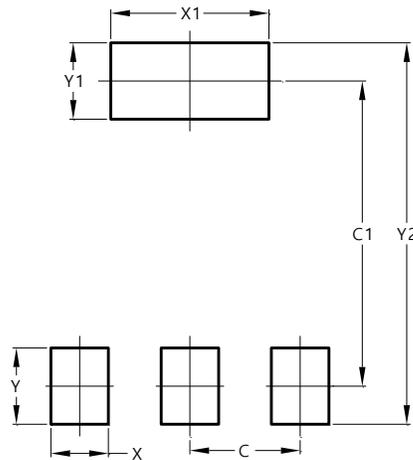


SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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